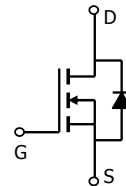
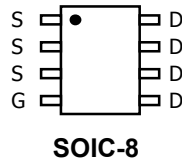


AO4430

N-Channel Enhancement Mode Field Effect Transistor

<p>General Description</p> <p>The 4430 uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity, body diode characteristics and ultra-low gate resistance. This device is ideally suited for use as a low side switch in Notebook CPU core power conversion. 4430 are electrically identical. -RoHS Compliant 4430 is Halogen Free</p>	<p>Features</p> <p>$V_{DS} (V) = 30V$ $I_D = 15A (V_{GS} = 10V)$ $R_{DS(ON)} < 8m\Omega (V_{GS} = 10V)$ $R_{DS(ON)} < 11m\Omega (V_{GS} = 4.5V)$</p>
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Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^A	I_D	15	A
Pulsed Drain Current ^B			
Power Dissipation	P_D	3	W
Avalanche Current ^B	I_{AR}	30	A
Repetitive avalanche energy 0.3mH ^B	E_{AR}	135	mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	59	75
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	16	24	$^\circ C/W$